Unit: mm

TOSHIBA GTR Module Silicon N Channel IGBT

MP6750

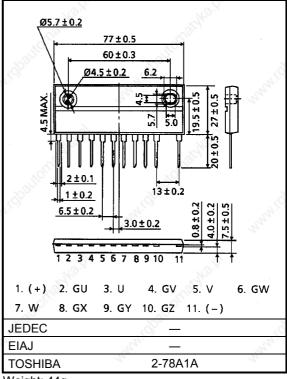
High Power Switching Applications Motor Control Applications

- The electrodes are isolated from case.
- 6 IGBTs are built into 1 package.
- Enhancement-mode
- Low saturation voltage

 $: V_{CE (sat)} = 4.0V (Max) (I_{C} = 15A)$

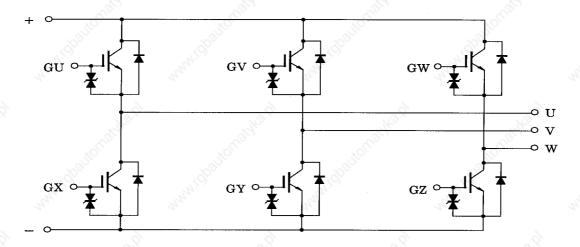
High speed : $t_f = 0.35 \mu s$ (Max) (IC = 15A)

 $t_{rr} = 0.15 \mu s \text{ (Max) (IF} = 15 \text{A)}$



Weight: 44g

Equivalent Circuit



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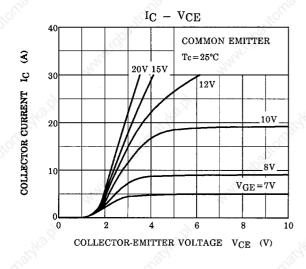
Maximum Ratings (Ta = 25°C)

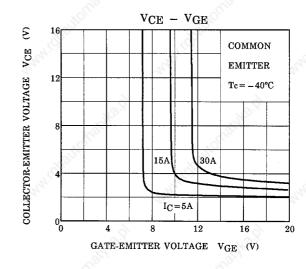
Characteristic Collector-emitter voltage Gate-emitter voltage		Symbol	Rating	Unit V V	
		V _{CES}	600		
		V _{GES}	± 20		
Collector current	DC	Ic	15	A	
	1ms	I _{CP}	30		
Forward current	DC	J _E	15	HOTT.	
	1ms	I _{FM}	30	» A	
Collector power dissipation (Tc = 25°C)		PC	55	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	~-40 ~ 125	°C	
Isolation voltage		V _{Isol}	2500 (AC 1 minute)	Asidy	
Screw torque		~9 <u>~</u>	1.5	N·m	

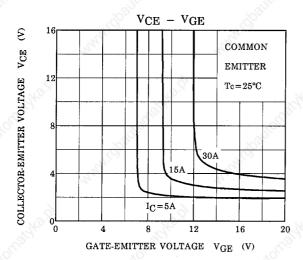
Electrical Characteristics (Ta = 25°C)

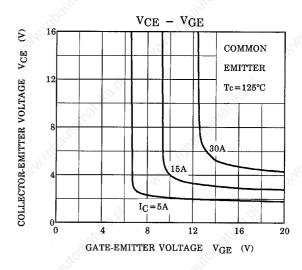
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage current		I _{GES}	V _{GE} = ± 20V, V _{CE} = 0	_	-6	± 20	μΑ	
Collector cut-off current		I _{CES}	V _{CE} = 600V, V _{GE} = 0	_	1710.	1.0	mA	
Gate-emitter cut-off voltage		V _{GE} (off)	I _C = 15mA, V _{CE} = 5V	3.0	_	6.0	V	
Collector-emitter saturation voltage		V _{CE (sat)}	I _C = 15A, V _{GE} = 15V	71.24.	3.0	4.0	V	
Input capacitance		C _{ies}	V _{CE} = 10V, V _{GE} = 0, f = 1MHz	_	1000	_	pF	
Switching time	Rise time	t _r	$\begin{array}{c c} & 1500 \\ & 1500 \\ & 1500 \\ & 3000 \end{array}$	_	0.3	0.6	μs	
	Turn-on time	t _{on}		_	0.4	0.8		
	Fall time	t _f		8	0.2	0.35		
	Turn-off time	t _{off}		144 A. J.	0.5	1.0		
Forward voltage		V _F	I _F = 15A, V _{GE} = 0	_	1.7	2.5	٧	
Reverse recovery time		t _{rr}	I _F = 15A, V _{GE} = -10V di / dt = 50A / μs	_	0.08	0.15	μs	
Thermal resistance		R _{th (j-c)}	Transistor	_	76/2	2.27	°C /\\	
			Diode		7770	3.09	°C/W	

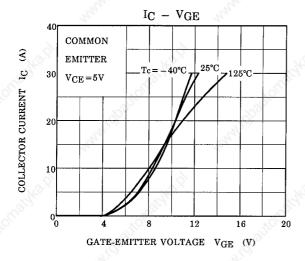
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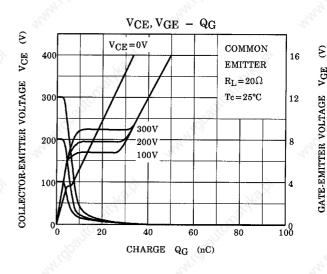


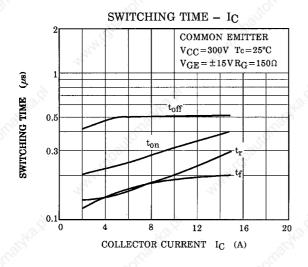


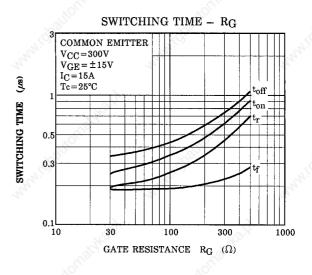


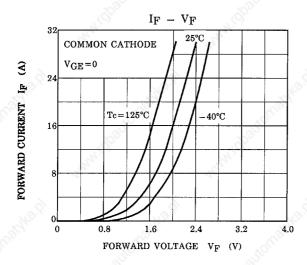


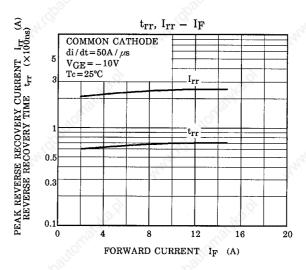


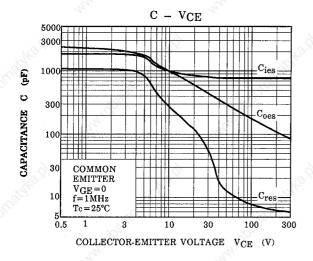


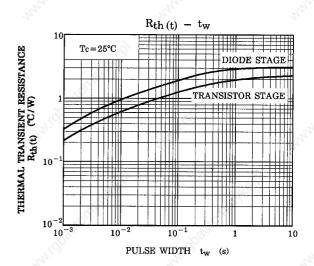


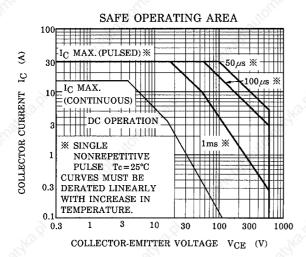


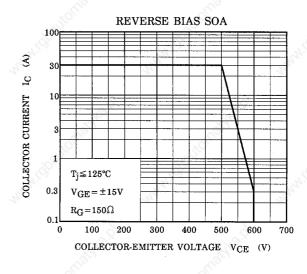












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